Razali Ismail

List of Publications by Year
in descending order

214	1,819	471509	361022
214 papers	1,819 citations	17 h-index	35 g-index
214 all docs	214 docs citations	214 times ranked	1658 citing authors

#	Article	IF	Citations
1	Conduction Mechanism of Valence Change Resistive Switching Memory: A Survey. Electronics (Switzerland), 2015, 4, 586-613.	3.1	520
2	Graphene Nanoribbon Conductance Model in Parabolic Band Structure. Journal of Nanomaterials, 2010, 2010, 1-4.	2.7	50
3	Analytical modeling of glucose biosensors based on carbon nanotubes. Nanoscale Research Letters, 2014, 9, 33.	5.7	50
4	Ballistic quantum transport in a nanoscale metal-oxide-semiconductor field effect transistor. Applied Physics Letters, 2007, 91, .	3.3	44
5	The Ultimate Ballistic Drift Velocity in Carbon Nanotubes. Journal of Nanomaterials, 2008, 2008, 1-8.	2.7	32
6	The drain velocity overshoot in an 80 nm metal-oxide-semiconductor field-effect transistor. Journal of Applied Physics, 2009, 105, 074503.	2.5	31
7	Graphene/Graphene Oxide-Based Ultrasensitive Surface Plasmon Resonance Biosensor. Plasmonics, 2017, 12, 1991-1997.	3.4	29
8	Photocatalytic degradation of 1,2-dichlorobenzene using immobilized TiO_2/SnO_2/WO_3 photocatalyst under visible light: Application of response surface methodology. Arabian Journal of Chemistry, 2018, 11, 34-47.	4.9	29
9	An analytical approach to model capacitance and resistance of capped carbon nanotube single electron transistor. AEU - International Journal of Electronics and Communications, 2018, 90, 97-102.	2.9	28
10	Ballistic mobility and saturation velocity in low-dimensional nanostructures. Microelectronics Journal, 2009, 40, 540-542.	2.0	26
11	Current–voltage characteristics of a silicon nanowire transistor. Microelectronics Journal, 2009, 40, 547-549.	2.0	23
12	Analytical modeling of trilayer graphene nanoribbon Schottky-barrier FET for high-speed switching applications. Nanoscale Research Letters, 2013, 8, 55.	5.7	23
13	Analytical prediction of liquid-gated graphene nanoscroll biosensor performance. RSC Advances, 2014, 4, 16153.	3.6	23
14	The high-field drift velocity in degenerately-doped silicon nanowires. International Journal of Nanotechnology, 2009, 6, 601.	0.2	22
15	Modelling of Graphene Nanoribbon Fermi Energy. Journal of Nanomaterials, 2010, 2010, 1-6.	2.7	20
16	Graphene Based Biosensor Model for <i>Escherichia Coli</i> Bacteria Detection. Journal of Nanoscience and Nanotechnology, 2017, 17, 601-605.	0.9	20
17	Gas adsorption effect on the graphene nanoribbon band structure and quantum capacitance. Adsorption, 2017, 23, 767-777.	3.0	19
18	Focused ion beam milling of exfoliated graphene for prototyping of electronic devices. Microelectronic Engineering, 2012, 98, 313-316.	2.4	17

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19	Single Electron Transistor Scheme Based on Multiple Quantum Dot Islands: Carbon Nanotube and Fullerene. ECS Journal of Solid State Science and Technology, 2018, 7, M145-M152.	1.8	17
20	Toxic metals in Perna viridis mussel and surface seawater in Pasir Gudang coastal area, Malaysia, and its health implications. Environmental Science and Pollution Research, 2018, 25, 30224-30235.	5.3	17
21	Quantum Capacitance Model for Graphene FET-Based Gas Sensor. IEEE Sensors Journal, 2019, 19, 3726-3732.	4.7	17
22	The Future of Non-planar Nanoelectronics MOSFET Devices: A Review. Journal of Applied Sciences, 2010, 10, 2136-2146.	0.3	17
23	Analytical modeling of high performance single-walled carbon nanotube field-effect-transistor. Microelectronics Journal, 2010, 41, 579-584.	2.0	16
24	Current Analysis and Modeling of Fullerene Single-Electron Transistor at Room Temperature. Journal of Electronic Materials, 2017, 46, 4294-4298.	2.2	16
25	Band gap engineering of BC_2N for nanoelectronic applications. Superlattices and Microstructures, 2017, 112, 328-338.	3.1	16
26	Analytical Modeling of Monolayer Graphene-based NO_2 Sensor. Sensor Letters, 2013, 11, 270-275.	0.4	16
27	Graphene Nanoribbon Field Effect Transistor Logic Gates Performance Projection. Journal of Computational and Theoretical Nanoscience, 2013, 10, 1164-1170.	0.4	15
28	Optimization of a Hydrothermal Growth Process for Low Resistance 1D Fluorine-Doped Zinc Oxide Nanostructures. Journal of Nanomaterials, 2019, 2019, 1-10.	2.7	15
29	Self-aligned vertical double-gate MOSFET (VDGM) with the oblique rotating ion implantation (ORI) method. Microelectronics Journal, 2008, 39, 1538-1541.	2.0	13
30	Carrier Statistics and Quantum Capacitance Models of Graphene Nanoscroll. Journal of Nanomaterials, 2014, 2014, 1-6.	2.7	13
31	Modeling and simulation of graphene-oxide-based RRAM. Journal of Computational Electronics, 2016, 15, 602-610.	2.5	13
32	Analysis and Modeling of Fullerene Single Electron Transistor Based on Quantum Dot Arrays at Room Temperature. Journal of Electronic Materials, 2018, 47, 4799-4806.	2.2	13
33	Ballistic Conductance Model of Bilayer Graphene Nanoribbon (BGN). Journal of Computational and Theoretical Nanoscience, 2011, 8, 1993-1998.	0.4	12
34	Sensitivity Modelling of Graphene Nanoscroll-Based NO2 Gas Sensors. Plasmonics, 2015, 10, 1133-1140.	3.4	12
35	Graphene nanoribbon field-effect transistor at high bias. Nanoscale Research Letters, 2014, 9, 604.	5.7	11
36	Carrier scattering and impact ionization in bilayer graphene. Journal of Computational Electronics, 2014, 13, 180-185.	2.5	11

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37	Method for polychlorinated biphenyls removal from mussels and its photocatalytic dechlorination. Applied Catalysis B: Environmental, 2017, 218, 327-337.	20.2	11
38	Analysis and Simulation of Coulomb Blockade and Coulomb Diamonds in Fullerene Single Electron Transistors. Journal of Nanoelectronics and Optoelectronics, 2018, 13, 138-143.	0.5	11
39	ENHANCEMENT OF NANO-RC SWITCHING DELAY DUE TO THE RESISTANCE BLOW-UP IN InGaAs. Nano, 2007, 02, 233-237.	1.0	10
40	Carbon nanotube conductance model in parabolic band structure. , 2010, , .		10
41	The Effect of Applied Voltage on the Carrier Effective Mass in ABA Trilayer Graphene Nanoribbon. Journal of Computational and Theoretical Nanoscience, 2012, 9, 1618-1621.	0.4	10
42	CHANNEL CONDUCTANCE OF ABA STACKING TRILAYER GRAPHENE NANORIBBON FIELD-EFFECT TRANSISTOR. Modern Physics Letters B, 2012, 26, 1250047.	1.9	10
43	Performance of Bilayer Graphene Nanoribbon Schottky Diode in Comparison with Conventional Diodes. Journal of Computational and Theoretical Nanoscience, 2013, 10, 323-327.	0.4	10
44	Electrical Property Analytical Prediction on Archimedes Chiral Carbon Nanoscrolls. Journal of Electronic Materials, 2016, 45, 5404-5411.	2.2	10
45	Investigating the electrical characteristics of a single electron transistor utilizing graphene nanoribbon as the island. Journal of Materials Science: Materials in Electronics, 2019, 30, 8007-8013.	2.2	10
46	Explicit continuous models of drain current, terminal charges and intrinsic capacitance for a long-channel junctionless nanowire transistor. Physica Scripta, 2019, 94, 105813.	2.5	10
47	The impact of vacancy defects on the performance of a single-electron transistor with a carbon nanotube island. Journal of Computational Electronics, 2019, 18, 428-435.	2.5	10
48	Scattering-limited and ballistic transport in a nano-CMOS circuit. Microelectronics Journal, 2009, 40, 581-583.	2.0	9
49	Enhanced performance analysis of vertical strained-sigeimpact Ionization MOSFET (VESIMOS). , 2012, , .		9
50	Analytical development and optimization of a graphene–solution interface capacitance model. Beilstein Journal of Nanotechnology, 2014, 5, 603-609.	2.8	9
51	Structure and Thickness Optimization of Active Layer in Nanoscale Organic Solar Cells. Plasmonics, 2015, 10, 495-502.	3.4	9
52	Analysis and modeling of quantum capacitance on graphene single electron transistor. International Journal of Modern Physics B, 2018, 32, 1850235.	2.0	9
53	The effects of a Stone–Wales defect on the performance of a graphene-nanoribbon-based Schottky diode. Journal of Computational Electronics, 2019, 18, 802-812.	2.5	9
54	Monolayer Graphene Nanoribbon Homojunction Characteristics. Science of Advanced Materials, 2012, 4, 753-756.	0.7	9

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55	Vertical Double Gate MOSFET For Nanoscale Device With Fully Depleted Feature. , 2009, , .		8
56	EFFECTIVE MOBILITY MODEL OF GRAPHENE NANORIBBON IN PARABOLIC BAND ENERGY. Modern Physics Letters B, 2011, 25, 739-745.	1.9	8
57	Perpendicular Electric Field Effect on Bilayer Graphene Carrier Statistic. Journal of Computational and Theoretical Nanoscience, 2013, 10, 1975-1978.	0.4	8
58	Analytical model for threshold voltage of double gate bilayer graphene field effect transistors. Microelectronics Reliability, 2014, 54, 44-48.	1.7	8
59	Influences of Sr-90 beta-ray irradiation on electrical characteristics of carbon nanoparticles. Journal of Applied Physics, 2016, 119, 124510.	2.5	8
60	Electrical Properties of MWCNT/HDPE Composite-Based MSM Structure Under Neutron Irradiation. Journal of Electronic Materials, 2017, 46, 2548-2555.	2.2	8
61	Performance analysis of one dimensional BC 2 N for nanoelectronics applications. Physica E: Low-Dimensional Systems and Nanostructures, 2018, 102, 33-38.	2.7	8
62	Analytical modelling and simulation of gas adsorption effects on graphene nanoribbon electrical properties. Molecular Simulation, 2018, 44, 551-557.	2.0	8
63	Modeling of quantum capacitance of Graphene Nanoribbons. , 2010, , .		7
64	Bilayer Graphene Nanoribbon Carrier Statistic in Degenerate and Non Degenerate Limit. Journal of Computational and Theoretical Nanoscience, 2011, 8, 2029-2032.	0.4	7
65	Investigation of incorporating dielectric pocket (DP) on Vertical Strained-SiGe Impact Ionization MOSFET (VESIMOS-DP). , 2012, , .		7
66	Quantum confinement effect on trilayer graphene nanoribbon carrier concentration. Journal of Experimental Nanoscience, 2014, 9, 51-63.	2.4	7
67	Structural and Properties of Graphene Nanobelts Rolled Up Into Spiral by a Single Graphene Sheet. Journal of Computational and Theoretical Nanoscience, 2014, 11, 601-606.	0.4	7
68	Carbon Nano-particle Synthesized by Pulsed Arc Discharge Method as a Light Emitting Device. Journal of Electronic Materials, 2018, 47, 4003-4009.	2.2	7
69	Scaling Challenges of Floating Gate Non-Volatile Memory and Graphene as the Future Flash Memory Device: A Review. Journal of Nanoelectronics and Optoelectronics, 2019, 14, 1195-1214.	0.5	7
70	A Unified Drainâ€"Current Model of Silicon Nanowire Field-Effect Transistor (SiNWFET) for Performance Metric Evaluation. Science of Advanced Materials, 2014, 6, 354-360.	0.7	7
71	Device Design Consideration for Nanoscale MOSFET Using Semiconductor TCAD Tools. , 2006, , .		6
72	Modeling of Quantum Capacitance in Graphene Nanoribbon. AIP Conference Proceedings, 2011, , .	0.4	6

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73	Schottky Current in Carbon Nanotube-Metal Contact. Journal of Computational and Theoretical Nanoscience, 2012, 9, 1554-1557.	0.4	6
74	Analytical modeling of the sensing parameters for graphene nanoscroll-based gas sensors. RSC Advances, 2015, 5, 54700-54709.	3.6	6
75	A new approach to model sensitivity of graphene-based gas sensors. Semiconductor Science and Technology, 2015, 30, 045012.	2.0	6
76	Graphene embedded surface plasmon resonance based sensor prediction model. Optical and Quantum Electronics, 2016, 48, 1.	3.3	6
77	Simulation and Fabrication of Extended Gate Ion Sensitive Field Effect Transistor for Biosensor Application. Communications in Computer and Information Science, 2012, , 396-403.	0.5	6
78	Monolayer Graphene Nanoribbon <I>p</I>â€"<I>n</I> Junction. Journal of Nanoengineering and Nanomanufacturing, 2012, 2, 375-378.	0.3	6
79	Performance and Microstructural Study on Soap Using Different Fatty Acids and Cations. Journal of Surfactants and Detergents, 2011, 14, 463-471.	2.1	5
80	Band energy effect on carrier velocity limit in graphene nanoribbon. Journal of Experimental Nanoscience, 2012, 7, 62-73.	2.4	5
81	Single and dual strained channel analysis of vertical strained — SiGe impact ionization MOSFET (VESIMOS). , 2013, , .		5
82	Analytical performance of 3â€°m and 3â€°m + 1 armchair graphene nanoribbons under uniaxial strain. Nanoscale Research Letters, 2014, 9, 598.	5.7	5
83	The Effect of Molecular Adsorption on Electro-Optical Properties of Graphene-Based Sensors. Plasmonics, 2017, 12, 1193-1198.	3.4	5
84	Preparation, characterization, and lead removal appraisal of zinc aluminate prepared at different calcination temperatures. Journal of the Chinese Chemical Society, 2018, 65, 1199-1209.	1.4	5
85	Analysis of Co-Tunneling Current in Fullerene Single-Electron Transistor. Brazilian Journal of Physics, 2018, 48, 406-410.	1.4	5
86	Experimental and theoretical investigation of sensing parameters in carbon nanotubeâ€based DNA sensor. IET Nanobiotechnology, 2018, 12, 1125-1129.	3.8	5
87	Future of Nanoscale Strained Si/SixGe1â€"x Metal-Oxide Semiconductor Field-Effect Transistor for Performance Metric Evaluation: A Review. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 317-326.	0.5	5
88	The Geometry Variation Effect on Carbon Atom Wire for Nano-Electronic Applications. Journal of Nanoelectronics and Optoelectronics, 2019, 14, 1120-1125.	0.5	5
89	Carrier Velocity in High-Field Transport of Trilayer Graphene Nanoribbon Field Effect Transistor. Science of Advanced Materials, 2014, 6, 633-639.	0.7	5
90	Modelling of the current-voltage characteristics of a carbon nano tube field effect transistor. , 2008, , .		4

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91	Formulation and simulation for electrical properties of a (5,3) Single Wall Carbon Nanotube. , 2008, , .		4
92	Body doping influence in vertical MOSFET design. , 2009, , .		4
93	CARBON NANOTUBE CAPACITANCE MODEL IN DEGENERATE AND NONDEGENERATE REGIMES. , 2011, , .		4
94	DRIFT VELOCITY AND MOBILITY OF A GRAPHENE NANORIBBON IN A HIGH MAGNITUDE ELECTRIC FIELD. , 2011, , .		4
95	BILAYER GRAPHENE NANORIBBON CARRIER STATISTICS IN THE DEGENERATE REGIME. , 2011, , .		4
96	LOW-FIELD MOBILITY MODEL ON PARABOLIC BAND ENERGY OF GRAPHENE NANORIBBON. Modern Physics Letters B, 2011, 25, 281-290.	1.9	4
97	QUANTUM CAPACITANCE EFFECT ON ZIG-ZAG GRAPHENE NANOSCROLLS (ZGNS) (16, 0). Modern Physics Letters B, 2013, 27, 1350002.	1.9	4
98	Band structures of graphene nanoscrolls and their dispersion relation near the Fermi point. RSC Advances, 2016, 6, 38753-38760.	3.6	4
99	Impact of Hydrogen Adsorption on the Performance of a Single Electron Transistor Utilizing Fullerene Quantum Dots. ECS Journal of Solid State Science and Technology, 2018, 7, M191-M194.	1.8	4
100	Effect of solution pH and adsorbent concentration on the sensing parameters of TGNâ€based electrochemical sensor. IET Nanobiotechnology, 2019, 13, 584-592.	3.8	4
101	Analysis and Modeling of White Graphene Physical Properties for Sensor Applications. Proceedings of the National Academy of Sciences India Section A - Physical Sciences, 2020, 90, 475-479.	1.2	4
102	Characterization of Strained Silicon MOSFET Using Semiconductor TCAD Tools. , 2006, , .		3
103	Silicon pillar thickness effect on vertical double gate MOSFET (VDGM) with oblique rotating implantation (ORI) method. , 2008, , .		3
104	Carrier velocity in carbon nano tube field effect transistor. , 2008, , .		3
105	Analysis and simulation of carriers statistic for semiconducting single wall carbon nanotube. Materials Research Innovations, 2009, 13, 211-213.	2.3	3
106	Ballistic Saturation Velocity of Quasi-2D Low-Dimensional Nanoscale Field Effect Transistor (FET). , 2009, , .		3
107	Threshold voltage roll-off modelling of bilayer graphene field-effect transistors. Semiconductor Science and Technology, 2013, 28, 125020.	2.0	3
108	The effect of uniaxial strain on graphene nanoribbon carrier statistic. Nanoscale Research Letters, 2013, 8, 479.	5.7	3

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109	Analytical Modeling and Artificial Neural Network (ANN) Simulation of Current-Voltage Characteristics in Graphene Nanoscroll Based Gas Sensors. Plasmonics, 2015, 10, 1713-1722.	3.4	3
110	Contact Effect on the Currentâ€"Voltage Characteristic of Graphene Nanoribbon Based Schottky Diode. Journal of Computational and Theoretical Nanoscience, 2015, 12, 478-483.	0.4	3
111	Explicit continuous charge-based compact model for long channel heavily doped surrounding-gate MOSFETs incorporating interface traps and quantum effects. Semiconductor Science and Technology, 2016, 31, 125020.	2.0	3
112	Carrier relaxation time modelling of monolayer black phosphorene. Micro and Nano Letters, 2017, 12, 758-762.	1.3	3
113	Effect of post annealing treatment on electrical and structural properties of zinc oxide nanostructures. Materials Today: Proceedings, 2019, 7, 710-714.	1.8	3
114	Impact of Chiral Indices on the Performance of Single Electron Transistor Utilizing Carbon Nanotube Island. ECS Journal of Solid State Science and Technology, 2019, 8, M26-M29.	1.8	3
115	A Review of Graphene Based Field Effect Transistor Architecture and Channel Geometry. Science of Advanced Materials, 2015, 7, 2011-2020.	0.7	3
116	Design and Simulation of 50 nm Vertical Double-Gate MOSFET (VDGM). , 2006, , .		2
117	The high-field drift velocity in degenerately-doped silicon nanowires. , 2008, , .		2
118	Investigation of pillar thickness variation effect on oblique rotating implantation (ORI)-based vertical double gate MOSFET. Microelectronics Journal, 2010, 41, 827-833.	2.0	2
119	Graphene Nanoribbon Fermi Energy Model in Parabolic Band Structure. , 2010, , .		2
120	A review on carbon-based materials as on-chip interconnects. Proceedings of SPIE, 2011, , .	0.8	2
121	Current-voltage modeling of Bilayer Graphene Nanoribbon Schottky Diode. , 2011, , .		2
122	Monolayer graphene nanoribbon p-n junction. , 2011, , .		2
123	The Effect of Interconnect on the Circuit Performance of 22 nm Graphene Nanoribbon Field Effect Transistor and MOSFET. Journal of Computational and Theoretical Nanoscience, 2013, 10, 1305-1309.	0.4	2
124	Geometry Effect on Graphene Nanoscrolls Band Gap. Journal of Computational and Theoretical Nanoscience, 2013, 10, 581-586.	0.4	2
125	The Effect of Bilayer Graphene Nanoribbon Geometry on Schottky-Barrier Diode Performance. Journal of Nanomaterials, 2013, 2013, 1-8.	2.7	2
126	Currentâ€"Voltage Characteristics of Bilayer Graphene Nanoribbon Field Effect Transistor. Journal of Computational and Theoretical Nanoscience, 2013, 10, 738-741.	0.4	2

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127	Strain effect on graphene nanoribbon carrier statistic in the presence of non-parabolic band structure. Chinese Physics B, 2016, 25, 096802.	1.4	2
128	Analytical study of the electronic properties of boron nitride nanosheet. , 2017, , .		2
129	Performance Evaluation of Silicon Nanowire Gate-All-Around Field-Effect Transistors and Their Dependence of Channel Length and Diameter. Science of Advanced Materials, 2015, 7, 190-198.	0.7	2
130	Modeling Trilayer Graphene-Based DET Characteristics for a Nanoscale Sensor. Advances in Computer and Electrical Engineering Book Series, 2017, , 19-38.	0.3	2
131	Graphene and CNT Field Effect Transistors Based Biosensor Models. Advances in Computer and Electrical Engineering Book Series, 2017, , 294-333.	0.3	2
132	Pre-silicon MOSFET mismatch modeling for early circuit simulations. , 2008, , .		1
133	Short channel effect of SOI vertical sidewall MOSFET. , 2008, , .		1
134	Characterization analysis of a novel approach in fabrication of CMOS compatible vertical MOSFETs incorporating a dielectric pocket. , 2008, , .		1
135	Analytical Study of Carrier Statistic in 2-Dimensional Nanoscale P-MOS. , 2009, , .		1
136	Analytical study of drift velocity in N-type silicon nanowires. , 2009, , .		1
137	Design and simulation analysis of nanoscale vertical MOSFET technology. , 2009, , .		1
138	Modeling of temperature variations in MOSFET mismatch for circuit simulations. , 2009, , .		1
139	Physics-Based Modelling of Ballistic Transport in Nanoscale Transistor. , 2009, , .		1
140	Artificial intelligence techniques for SPICE optimization of MOSFET modeling. , 2009, , .		1
141	Physics-Based Simulation of Carrier Velocity in 2-Dimensional P-Type MOSFET. , 2009, , .		1
142	Numerical Simulation Characterization of 50nm MOSFET Incorporating Dielectric Pocket (DP-MOSFET). , 2010, , .		1
143	CARBON NANOTUBE BAND STRUCTURE EFFECT ON CARBON NANOTUBE FIELD EFFECT TRANSISTOR. , 2010, , .		1
144	Enhanced performance of vertical double gate MOSFET (VDGM) with oblique rotating implantation (ORI) method. , 2010, , .		1

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145	Reduced parasitic capacitances analysis of nanoscale vertical MOSFET. , 2010, , .		1
146	Single Wall Carbon Nanotube Field Effect Transistor Model. Journal of Computational and Theoretical Nanoscience, 2011, 8, 261-267.	0.4	1
147	Effect of Graphene Nanoribbons Layers on Its Band Energy and the Electrical Properties. Journal of Computational and Theoretical Nanoscience, 2012, 9, 2082-2085.	0.4	1
148	Two Dimensional Analytical Threshold Voltage Model of Nanoscale Strained Si/Si_{1â€"<I>x</I>} Ge_{<I>x</I>} MOSFETs Including Quantum Mechanical Effects. Journal of Computational and Theoretical Nanoscience, 2012, 9, 441-447.	0.4	1
149	Schottky barrier lowering effect on graphene nanoribbon based schottky diode. , 2013, , .		1
150	Quantum Mechanical Effects on the Threshold Voltage of Nanoscale Dual Channel Strained Si/Strained Si<SUB>1â€"<I>y</I></SUB>Ge<SUB><I>y</I></SUB>/Relaxed <I>Si</I><SUB>1â€"<I>x</I></SUB>Ge<SUB><I>x</I></SUB>MOSFETs. Journal of Computational and Theoretical Nanoscience, 2013, 10, 1231-1235.	0.4	1
151	Bilayer Graphene Nanoribbon Mobility Model in Ballistic Transport Limit. Journal of Computational and Theoretical Nanoscience, 2013, 10, 1262-1265.	0.4	1
152	An Analytic Model for Estimating the Length of the Velocity Saturated Region in Double Gate Bilayer Graphene Transistors. Journal of Nanomaterials, 2013, 2013, 1-5.	2.7	1
153	The impact of germanium in strained Si/relaxed Si_{1â^<i>x</i>}Ge_{<i>x</i>}on carrier performance in non-degenerate and degenerate regimes. Journal of Semiconductors, 2013, 34, 062001.	3.7	1
154	The effect of width on graphene nanoribbon density of state under uniaxial strain. , 2013, , .		1
155	ENERGY QUANTIZATION ON THE CURRENT-VOLTAGE CHARACTERISTIC OF NANOSCALE TWO-DIMENSIONAL MOSFET. International Journal of Modern Physics B, 2013, 27, 1350077.	2.0	1
156	Modeling of Nanodevices and Nanostructures. Journal of Nanomaterials, 2014, 2014, 1-2.	2.7	1
157	Unified Drain Current Model of Armchair Graphene Nanoribbons with Uniaxial Strain and Quantum Effect. Journal of Nanomaterials, 2014, 2014, 1-7.	2.7	1
158	Analytical study of subthreshold behaviour of double gate bilayer graphene field effect transistors. Semiconductor Science and Technology, 2014, 29, 115011.	2.0	1
159	Performance benchmarking of graphene nanoscroll transistor with 22nm MOSFET model. , 2015, , .		1
160	Performance prediction of Graphene Nanoscroll and Carbon Nanotube transistors. , 2016, , .		1
161	A carrier velocity model for electrical detection of gas molecules. Beilstein Journal of Nanotechnology, 2019, 10, 644-653.	2.8	1
162	Stacking SiO₂/ High-K Dielectric Material in 30nm Junction-less Nanowire Transistor Optimized Using Taguchi Method for Lower Leakage Current. , 2019, , .		1

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163	The Potential Barrier of Graphene Nanoribbon Based Schottky Diode. Journal of Nanoelectronics and Optoelectronics, 2013, 8, 281-284.	0.5	1
164	Modelling Effective Charge Density in Graphene-Based DNA Sensor. Science of Advanced Materials, 2016, 8, 1187-1194.	0.7	1
165	Design and Simulation of a High Performance Lateral BJTs on TFSOI. , 2006, , .		0
166	Ballistic carrier transport in a quasi-two-dimensional nanoscale field effect transistor (FET). , 2008, , .		0
167	Self-aligned double-gate (DG) vertical MOSFET’s using oblique rotating implantation (ORI) method with reduced parasitic capacitance. , 2008, , .		0
168	The Ultimate Drift Velocity in Two Dimensional Quantum Limit. , 2008, , .		0
169	Analytical Study Of Drift Velocity In P-Type Silicon Nanowires. , 2009, , .		0
170	Extraction of SPICE Model for Double Gate Vertical MOSFET. , 2009, , .		0
171	Design and Analysis of Nanoscale Vertical MOSFET Using Oblique Rotating Implantation (ORI) Method with Reduced Parasitic Capacitance. , 2009, , .		0
172	FERMI ENERGY IN THE NON-PARABOLIC BAND STRUCTURE OF A CARBON NANOTUBE. , 2009, , .		0
173	Numerical Analysis of Vertical Double Gate MOSFETs (VDGM) With Dielectric Pocket (DP) Effects on Silicon Pillar for Nanoscale Transistor. , 2009, , .		0
174	Numerical Simulation Analysis of CMOS Compatible Process of 50 nm Vertical Single and Double Gate NMOSFET. , 2010, , .		0
175	The Corner Effects of a Curved-Channel MOSFET. , 2010, , .		0
176	Bilayer Graphene nanoribbon conductance model in parabolic band structure. , 2010, , .		0
177	Nonparabolic band structure effect on carrier transport in semiconducting graphene nanoribbons. , 2010, , .		0
178	Investigation of short channel immunity of fully depleted double gate MOS with vertical structure. , 2010, , .		0
179	The influence of body-tied and floating-body structure in Double Gate Vertical n-MOSFET. , 2010, , .		0
180	Biased voltage boundary condition to operate Bilayer Graphene in the insulating region. , 2011, , .		0

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181	An Analytical Threshold Voltage Model for the Vertical Sidewall Mosfet with a Curved-Channel. Journal of Computational and Theoretical Nanoscience, 2011, 8, 2299-2306.	0.4	0
182	Influence of Body-Tied and Floating-Body Structure in Double Gate Vertical n-MOSFET. , 2011, , .		0
183	Bilayer Graphene Nanoribbon Conductance Model in Parabolic Band Structure. , 2011, , .		0
184	Improved dead time response for Si Avalanche Photodiode. , 2012, , .		0
185	Simulation of nanoscale dual-channel strained Si/Strained Si$_{1-y}$Ge$_{y}$/Relaxed Si$_{1-x}$Ge$_{x}$ PMOSFET. , 2012, , .		0
186	Temperature effect on quantum capacitance zig-zag graphene nanoscrolls (ZGNS) (16,0). , 2012, , .		0
187	Modeling of Drain Current for Grooved-Gate MOSFET. Journal of Computational and Theoretical Nanoscience, 2012, 9, 1596-1602.	0.4	0
188	Simulation of Trigate FET with Semi-Cylindrical Channel to Reduce Corner Effect. , 2013, , .		0
189	Performance Analysis of Vertical Strained-SiGe Impact Ionization MOSFET Incorporating Dielectric Pocket (VESIMOS-DP). , 2013, , .		0
190	Mobility enhancement on Vertical Strained-SiGe Impact Ionization MOSFET incorporating Dielectric Pocket (VESIMOS-DP). , 2013, , .		0
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